



IN THE CLAIMS

Please amend the claim 1 to read as follows:

B.1
1. (Amended) A bottom-gate thin-film transistor comprising a gate electrode, a gate insulating film, an active layer, and a protective insulating film deposited in that order on a substrate; and

various layers formed over said protective film with at least one electrode extending therethrough that is operatively and electrically connected to said active layer, LDD region or source-drain region;

wherein,

the protective insulating film has a thickness of 100 nm or less, and the protective insulating film is formed on any one of the active layer, an LDD region, and a source-drain region, and

there is no etched mask structure within the thin-film transistor structure.